

# Hai Lu

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5224751/publications.pdf>

Version: 2024-02-01

144  
papers

3,046  
citations

172457

29  
h-index

197818

49  
g-index

147  
all docs

147  
docs citations

147  
times ranked

3673  
citing authors

#	ARTICLE	IF	CITATIONS
1	A self-powered high-performance graphene/silicon ultraviolet photodetector with ultra-shallow junction: breaking the limit of silicon?. Npj 2D Materials and Applications, 2017, 1, .	7.9	211
2	Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. Light: Science and Applications, 2021, 10, 94.	16.6	193
3	Anomalous Terahertz Reflection and Scattering by Flexible and Conformal Coding Metamaterials. Advanced Optical Materials, 2015, 3, 1374-1380.	7.3	175
4	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase $\text{In}_{1-x}\text{Ga}_x\text{O}_{2-x}\text{O}_3$ /ZnO Isotype Heterostructures. ACS Applied Materials & Interfaces, 2017, 9, 36997-37005.	8.0	158
5	Carbonized Bamboos as Excellent 3D Solar Vapor Generation Devices. Advanced Materials Technologies, 2019, 4, 1800593.	5.8	107
6	High-Gain AlGaIn Solar-Blind Avalanche Photodiodes. IEEE Electron Device Letters, 2014, 35, 372-374.	3.9	97
7	Developing LED UV fluorescence sensors for online monitoring DOM and predicting DBPs formation potential during water treatment. Water Research, 2016, 93, 1-9.	11.3	89
8	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. Applied Physics Letters, 2012, 100, 243505.	3.3	82
9	1.37 kV/12 A $\text{NiO}/\text{In}_{0.2}\text{Ga}_{0.8}\text{O}_3$ Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. IEEE Transactions on Power Electronics, 2021, 36, 12213-12217.	7.9	77
10	Ultra-Low Dark Current AlGaIn-Based Solar-Blind Metal-Semiconductor-Metal Photodetectors for High-Temperature Applications. IEEE Sensors Journal, 2012, 12, 2086-2090.	4.7	75
11	Br doped porous bismuth oxychloride micro-sheets with rich oxygen vacancies and dominating $\{111\}$ facets for enhanced nitrogen photo-fixation performances. Journal of Colloid and Interface Science, 2019, 556, 111-119.	9.4	66
12	1.95-kV Beveled-Mesa $\text{NiO}/\text{In}_{0.2}\text{Ga}_{0.8}\text{O}_3$ Heterojunction Diode With 98.5% Conversion Efficiency and Over Million-Times Overvoltage Ruggedness. IEEE Transactions on Power Electronics, 2022, 37, 1223-1227.	7.9	60
13	Highly Efficient Spintronic Terahertz Emitter Enabled by Metal-Dielectric Photonic Crystal. Advanced Optical Materials, 2018, 6, 1800965.	7.3	59
14	High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. IEEE Photonics Technology Letters, 2014, 26, 1136-1138.	2.5	53
15	Solvent-Based Soft Patterning of Graphene Lateral Heterostructures for Broadband High-Speed Metal-Semiconductor-Metal Photodetectors. Advanced Materials Technologies, 2017, 2, 1600241.	5.8	53
16	Sustainable Solar Evaporation while Salt Accumulation. ACS Applied Materials & Interfaces, 2021, 13, 4935-4942.	8.0	46
17	High Quantum Efficiency GaN-Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. IEEE Photonics Technology Letters, 2013, 25, 652-654.	2.5	45
18	Highly selective and sensitive phosphate anion sensors based on AlGaIn/GaN high electron mobility transistors functionalized by ion imprinted polymer. Scientific Reports, 2016, 6, 27728.	3.3	43

#	ARTICLE	IF	CITATIONS
19	A Reusable and High Sensitivity Nitrogen Dioxide Sensor Based on Monolayer SnSe. IEEE Electron Device Letters, 2018, 39, 599-602.	3.9	43
20	Field-dependent carrier trapping induced kink effect in AlGaIn/GaN high electron mobility transistors. Applied Physics Letters, 2011, 98, .	3.3	40
21	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. ACS Applied Materials & Interfaces, 2019, 11, 20956-20964.	8.0	39
22	Do all screw dislocations cause leakage in GaN-based devices?. Applied Physics Letters, 2020, 116, .	3.3	38
23	A flexible wideband bandpass terahertz filter using multi-layer metamaterials. Applied Physics B: Lasers and Optics, 2013, 113, 285-290.	2.2	36
24	Sustainable Application of ZIF-8 for Heavy-Metal Removal in Aqueous Solutions. Sustainability, 2021, 13, 984.	3.2	36
25	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. Advanced Materials, 2020, 32, e1904354.	21.0	34
26	Vertically Emitting Indium Phosphide Nanowire Lasers. Nano Letters, 2018, 18, 3414-3420.	9.1	33
27	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. IEEE Electron Device Letters, 2014, 35, 1034-1036.	3.9	30
28	Significant Performance Improvement in AlGaIn Solar-Blind Avalanche Photodiodes by Exploiting the Built-In Polarization Electric Field. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 187-192.	2.9	30
29	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. IEEE Electron Device Letters, 2021, 42, 974-977.	3.9	29
30	An ultra-sensitive and selective nitrogen dioxide sensor based on a novel $P_{2C_2}$ monolayer from a theoretical perspective. Nanoscale, 2018, 10, 21936-21943.	5.6	28
31	Exploitation of Polarization in Back-Illuminated AlGaIn Avalanche Photodiodes. IEEE Photonics Technology Letters, 2013, 25, 1510-1513.	2.5	25
32	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	3.3	24
33	Modification of the valence band structures of polar and nonpolar plane wurtzite-GaN by anisotropic strain. Journal of Applied Physics, 2009, 106, 023714.	2.5	23
34	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. Scientific Reports, 2016, 6, 23486.	3.3	21
35	Gate Reliability of p-GaN Gate AlGaIn/GaN High Electron Mobility Transistors. IEEE Electron Device Letters, 2019, 40, 379-382.	3.9	21
36	Characteristics of polarization-doped N-face III-nitride light-emitting diodes. Applied Physics Letters, 2012, 100, 073507.	3.3	20

#	ARTICLE	IF	CITATIONS
37	Guided Bloch surface wave resonance for biosensor designs. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 2016, 33, 997.	1.5	20
38	High- $\kappa$ HfO <sub>2</sub> -Based AlGaIn/GaN MIS-HEMTs With Y <sub>2</sub> O <sub>3</sub> Interfacial Layer for High Gate Controllability and Interface Quality. IEEE Journal of the Electron Devices Society, 2020, 8, 15-19.	2.1	19
39	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. IEEE Transactions on Power Electronics, 2021, 36, 12163-12167.	7.9	19
40	70- $\mu$ m-Body Ga <sub>2</sub> O <sub>3</sub> Schottky Barrier Diode With 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. IEEE Electron Device Letters, 2022, 43, 773-776.	3.9	19
41	Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CH <sub>3</sub> NH <sub>3</sub> Pb(BrxI <sup>1-x</sup> ) <sub>3</sub> Crystals Synthesized via a Solvothermal Method. Scientific Reports, 2017, 7, 17695.	3.3	18
42	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. IEEE Transactions on Power Electronics, 2022, 37, 26-30.	7.9	18
43	Solar-blind ultraviolet AlInN/AlGaIn distributed Bragg reflectors. Applied Physics Letters, 2013, 102, .	3.3	17
44	Optical Tamm states in hetero-structures with highly dispersive planar plasmonic metamaterials. Applied Physics Letters, 2013, 102, .	3.3	17
45	$V_T$ Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. IEEE Electron Device Letters, 2021, 42, 1508-1511.	3.9	17
46	Higher-order exceptional point and Landau-Zener Bloch oscillations in driven non-Hermitian photonic Lieb lattices. APL Photonics, 2021, 6, .	5.7	17
47	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. IEEE Photonics Technology Letters, 2016, 28, 2526-2528.	2.5	16
48	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. IEEE Photonics Technology Letters, 2016, 28, 1189-1192.	2.5	16
49	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. IEEE Transactions on Electron Devices, 2017, 64, 4532-4539.	3.0	16
50	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. IEEE Electron Device Letters, 2020, 41, 469-472.	3.9	16
51	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. IEEE Photonics Journal, 2016, 8, 1-7.	2.0	15
52	A Terahertz Controlled NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. Advanced Optical Materials, 2017, 5, 1700108.	7.3	15
53	$\mu$ -Ga <sub>2</sub> O <sub>3</sub> : A Promising Candidate for High-Electron-Mobility Transistors. IEEE Electron Device Letters, 2020, , 1-1.	3.9	15
54	Tunneling-Hopping Transport Model for Reverse Leakage Current in InGaIn/GaN Blue Light-Emitting Diodes. IEEE Photonics Technology Letters, 2017, 29, 1447-1450.	2.5	14

#	ARTICLE	IF	CITATIONS
55	Enhanced Diffuse Reflectance and Microstructure Properties of Hybrid Titanium Dioxide Nanocomposite Coating. <i>Nanoscale Research Letters</i> , 2018, 13, 328.	5.7	14
56	Improving the sensitivity of compound waveguide grating biosensor via modulated wavevector. <i>Applied Physics Express</i> , 2018, 11, 082202.	2.4	14
57	Observation of quincunx-shaped and dipole-like flatband states in photonic rhombic lattices without band-touching. <i>APL Photonics</i> , 2020, 5, 016107.	5.7	14
58	High-Responsivity and Fast-Response Ultraviolet Phototransistors Based on Enhanced p-GaN/AlGaIn/GaN HEMTs. <i>ACS Photonics</i> , 2022, 9, 2040-2045.	6.6	14
59	An Improved Design for Solar-Blind AlGaIn Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	2.0	13
60	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	2.0	13
61	High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , 2018, 18, 1314.	3.8	13
62	Janus Ga <sub>2</sub> SeTe: A Promising Candidate for Highly Efficient Solar Cells. <i>Solar Rrl</i> , 2019, 3, 1900321.	5.8	13
63	Enhanced Contactless Salt-Collecting Solar Desalination. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 34151-34158.	8.0	13
64	GaN MSM photodetectors fabricated on bulk GaN with low dark current and high UV/visible rejection ratio. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2473-2475.	0.8	12
65	Metamaterials: Anomalous Terahertz Reflection and Scattering by Flexible and Conformal Coding Metamaterials ( <i>Advanced Optical Materials</i> 10/2015). <i>Advanced Optical Materials</i> , 2015, 3, 1373-1373.	7.3	11
66	Near-infrared ITO-based photonic hypercrystals with large angle-insensitive bandgaps. <i>Optics Letters</i> , 2022, 47, 917.	3.3	11
67	M-Plane $\pm$ -Ga <sub>2</sub> O <sub>3</sub> Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. <i>IEEE Electron Device Letters</i> , 2022, 43, 541-544.	3.9	11
68	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. <i>IEEE Photonics Technology Letters</i> , 2017, 29, 1603-1606.	2.5	10
69	Guided Bloch surface wave resonance by near normal and near in-plane illuminations: the hyper azimuthal sensitivity. <i>Optics Express</i> , 2018, 26, 12769.	3.4	10
70	Precise Extraction of Dynamic $\langle i \rangle_{\text{dson}}$ Under High Frequency and High Voltage by a Double-Diode-Isolation Method. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 690-695.	2.1	10
71	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. <i>IEEE Electron Device Letters</i> , 2019, 40, 1929-1932.	3.9	10
72	Performance Modulation for Back-Illuminated AlGaIn Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. <i>IEEE Photonics Journal</i> , 2019, 11, 1-7.	2.0	10

#	ARTICLE	IF	CITATIONS
73	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. IEEE Photonics Technology Letters, 2020, 32, 791-794.	2.5	10
74	Nonreciprocal Tamm plasmon absorber based on lossy epsilon-near-zero materials. Optics Express, 2021, 29, 17736.	3.4	10
75	Low emissivity double sides antireflection coatings for silicon wafer at infrared region. Journal of Alloys and Compounds, 2018, 742, 729-735.	5.5	9
76	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. IEEE Photonics Technology Letters, 2018, 30, 805-808.	2.5	9
77	Over 1200 V Normally-OFF p-NiO Gated AlGaIn/GaN HEMTs on Si With a Small Threshold Voltage Shift. IEEE Electron Device Letters, 2022, 43, 268-271.	3.9	9
78	High-Quality Crystal Growth and Characteristics of AlGaIn-Based Solar-Blind Distributed Bragg Reflectors with a Tri-layer Period Structure. Scientific Reports, 2016, 6, 29571.	3.3	8
79	Fine Control of the Electric Field Distribution in the Heterostructure Multiplication Region of AlGaIn Avalanche Photodiodes. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	8
80	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. IEEE Photonics Journal, 2017, 9, 1-8.	2.0	8
81	Plasmonic interference lithography by coupling the bulk plasmon polariton mode and the waveguide mode. Journal Physics D: Applied Physics, 2020, 53, 135103.	2.8	8
82	Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. IEEE Photonics Technology Letters, 2012, 24, 2203-2205.	2.5	7
83	The Fano-type transmission and field enhancement in heterostructures composed of epsilon-near-zero materials and truncated photonic crystals. Applied Physics Letters, 2013, 103, 201902.	3.3	7
84	Light tunneling effect tuned by a meta-interface with electromagnetically-induced-transparency-like properties. Applied Physics Letters, 2013, 102, .	3.3	7
85	Surface Acceptor-Like Trap Model for Gate Leakage Current Degradation in Lattice-Matched InAlN/GaN HEMTs. IEEE Electron Device Letters, 2015, 36, 1281-1283.	3.9	7
86	High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 374-377.	0.8	7
87	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800069.	1.8	7
88	Enhanced nonlinear optical response of a planar thick metal film combined with a truncated photonic crystal. Optics Communications, 2012, 285, 5416-5419.	2.1	6
89	Reverse leakage current in AlGaIn-based ultraviolet light-emitting diodes. Science Bulletin, 2014, 59, 1276-1279.	1.7	6
90	Metasurface-enhanced optical Tamm states and related lasing effect. Journal of the Optical Society of America B: Optical Physics, 2015, 32, 1624.	2.1	6

#	ARTICLE	IF	CITATIONS
91	Noise Characterization of Geiger-Mode 4H-SiC Avalanche Photodiodes for Ultraviolet Single-Photon Detection. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-5.	2.9	6
92	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. IEEE Photonics Technology Letters, 2019, 31, 447-450.	2.5	6
93	Content and health risk assessment of heavy metals and polybrominated diphenyl ethers in fish from Songhua Lake (Jilin City), China. Environmental Science and Pollution Research, 2020, 27, 40848-40856.	5.3	6
94	Quasiperiodic metamaterials empowered non-metallic broadband optical absorbers. Optics Express, 2021, 29, 13576.	3.4	6
95	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability. , 2021, , .		6
96	Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGaIn/GaN HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700368.	1.8	5
97	Investigation on the Activation Energy of Device Degradation and Switching Time in AlGaIn/GaN HEMTs for High-Frequency Application. IEEE Journal of the Electron Devices Society, 2019, 7, 417-424.	2.1	5
98	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. IEEE Photonics Technology Letters, 2020, 32, 706-709.	2.5	5
99	A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. IEEE Photonics Journal, 2021, 13, 1-8.	2.0	5
100	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. Journal of Applied Physics, 2020, 128, .	2.5	5
101	Fabrication of blue and green non-polar InGaIn/GaN multiple quantum well light-emitting diodes on LiAlO <sub>2</sub> (100) substrates. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1404-1406.	1.8	4
102	High-efficiency nonlinear platform with usage of metallic nonlinear susceptibility. Optics Letters, 2013, 38, 1283.	3.3	4
103	Sex- and season-dependent differences in telomere length and telomerase activity in the leaves of ash and willow. SpringerPlus, 2014, 3, 163.	1.2	4
104	The Generalized Analytical Expression for the Resonance Frequencies of Plasmonic Nanoresonators Composed of Folded Rectangular Geometries. Scientific Reports, 2019, 9, 52.	3.3	4
105	Observation and Modeling of Leakage Current in AlGaIn Ultraviolet Light Emitting Diodes. IEEE Photonics Technology Letters, 2019, 31, 1697-1700.	2.5	4
106	Effects of dissipative substrate on the performances of enhancement mode AlInN/GaN HEMTs. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2019, 32, e2482.	1.9	4
107	Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900729.	1.8	4
108	Band evolution and Landau-Zener Bloch oscillations in strained photonic rhombic lattices. Optics Express, 2021, 29, 37503.	3.4	4

#	ARTICLE	IF	CITATIONS
109	Developing a Miniaturized Spectrophotometer Using 235 and 275 nm UVC-LEDs for Fast Detection of Nitrate in Natural Water and Wastewater Effluents. <i>ACS ES&amp;T Water</i> , 2021, 1, 2548-2555.	4.6	4
110	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , 2021, 42, 1743-1746.	3.9	4
111	Self-Assembly Nanopillar/Superlattice Hierarchical Structure: Boosting AlGaIn Crystalline Quality and Achieving High-Performance Ultraviolet Avalanche Photodetector. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 33525-33537.	8.0	4
112	Polarization-independent wide-angle flexible multiband thermal emitters enabled by layered quasi-periodic photonic crystal. <i>Optics and Laser Technology</i> , 2022, 156, 108474.	4.6	4
113	Improvements in Microstructure and Leakage Current of High-In-Content InGaIn p-i-n Structure by Annealing. <i>IEEE Photonics Technology Letters</i> , 2012, 24, 1478-1480.	2.5	3
114	Electronic properties of arsenene nanoribbons for FET application. <i>Optical and Quantum Electronics</i> , 2020, 52, 1.	3.3	3
115	Different $I_{on}/I_{off}$ Behaviors and Leakage Current Mechanisms in AlGaIn Solar-Blind Ultraviolet Avalanche Photodiodes. <i>ACS Applied Electronic Materials</i> , 2020, 2, 2716-2720.	4.3	3
116	Energy Consumption Analysis of Sludge Transport Pipeline System Based on GA-DE Hybrid Algorithm. <i>Journal of Chemical Engineering of Japan</i> , 2014, 47, 621-627.	0.6	3
117	Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. <i>IEEE Electron Device Letters</i> , 2021, 42, 1755-1758.	3.9	3
118	A method of applying compressive pre-stress to AlGaIn barrier in AlGaIn/GaN heterostructures by depositing an additional thermally mismatched dielectric. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 2474-2478.	1.8	2
119	Polarization-independent split bullseye antennas for infrared nano-photodetectors. <i>Scientific Reports</i> , 2016, 6, 39106.	3.3	2
120	Photodetectors: Solvent-Based Soft Patterning of Graphene Lateral Heterostructures for Broadband High-Speed Metal-Semiconductor-Metal Photodetectors ( <i>Adv. Mater. Technol.</i> 2/2017). <i>Advanced Materials Technologies</i> , 2017, 2, .	5.8	2
121	Numerical study of the defect adamantine compound CuGaGeSe <sub>4</sub> . <i>Molecular Physics</i> , 2018, 116, 1551-1557.	1.7	2
122	Second-harmonic generation from 2D photonic crystal waveguide with simultaneous near-flat dispersions at fundamental frequency and second harmonic. <i>Optics Communications</i> , 2020, 472, 125885.	2.1	2
123	Interface roughness governed negative magnetoresistances in two-dimensional electron gases in AlGaIn/GaN heterostructures. <i>Physical Review Materials</i> , 2021, 5, .	2.4	2
124	4H-SiC n-i-p Extreme Ultraviolet Detector With Gradient Doping-Induced Surface Junction. <i>IEEE Electron Device Letters</i> , 2022, 43, 906-909.	3.9	2
125	ITO-based metamaterials for polarization-independent wide-angle mid-infrared thermal radiation. <i>Case Studies in Thermal Engineering</i> , 2022, 37, 102278.	5.7	2
126	InGaIn/GaN multi-quantum-well-based light-emitting and photodetective dual-functional devices. <i>Frontiers of Optoelectronics in China</i> , 2009, 2, 442-445.	0.2	1



#	ARTICLE	IF	CITATIONS
127	Structural and optical characteristics of Al <sub>x</sub> Ga <sub>1-x</sub> N/AlN superlattice. Science in China Series D: Earth Sciences, 2009, 52, 332-335.	0.9	1
128	Effective suppression of the high temperature DC performance degradation of AlInN/GaN HEMTs by back barrier. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2018, 31, e2299.	1.9	1
129	Azimuthal illumination enabled ultra-high polar angle sensitivity by a Bloch surface wave resonance refractive index sensor. Journal Physics D: Applied Physics, 2020, 53, 215401.	2.8	1
130	Using a Modified Turian's Yuan Model to Enhance Heterogeneous Resistance in Municipal Sludge Transportation Pipeline. ACS Omega, 2021, 6, 7199-7211.	3.5	1
131	An Ultraviolet Photon Counting Imaging System Based on a SiC SPAD Array. IEEE Photonics Technology Letters, 2021, 33, 1213-1216.	2.5	1
132	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. , 0, .		1
133	3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. IEEE Transactions on Electron Devices, 2022, 69, 1918-1923.	3.0	1
134	Strain- and Compositional Modulation of the Near-Band-Edge Band Structures of AlN and Its Ternary Alloys with GaN and InN. , 2009, , .		0
135	Plasmonic Fraunhofer-wavelength narrow-band filter based on calcium film. Optik, 2014, 125, 3355-3357.	2.9	0
136	Determination of Temperature-Dependent Stress State in Thin AlGaIn Layer of AlGaIn/GaN HEMT Heterostructures by Near-Resonant Raman Scattering. Advances in Condensed Matter Physics, 2015, 2015, 1-6.	1.1	0
137	Improved Schottky contacts to InGaIn alloys by a photoelectrochemical treatment. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1034-1038.	1.8	0
138	Frequency response and design consideration of GaN SAM avalanche photodiodes. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	0
139	Chiral Metamaterials: A Terahertz Controlled NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials (Advanced Optical Materials 18/2017). Advanced Optical Materials, 2017, 5, .	7.3	0
140	Abnormal mode splitting in photonic crystals micro-cavity containing highly dispersive metamaterials. Journal of Optics (United Kingdom), 2017, 19, 125101.	2.2	0
141	Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2070028.	1.8	0
142	46.4: Fabrication of InGaIn/GaN-based nano LEDs for display applications. Digest of Technical Papers SID International Symposium, 2021, 52, 568-568.	0.3	0
143	An experimental study on the pretreatment of lignite upgrading wastewater using the Fenton oxidation method. Chemical Papers, 0, , 1.	2.2	0
144	The generating and modulating characteristics of bound states in the continuum for both TE and TM polarizations by one-dimensional photonic crystal slabs. Journal of Optics (United Kingdom), 2021, 23, 105202.	2.2	0